



100V NPN ULTRA-LOW VCE(sat) TRANSISTOR IN PowerDI3333-8

Features

- BVcEo > 100V
- BV_{EBO} > 8V
- Continuous Current Ic to 5.5A
- Peak Pulse Current Icm to 10A
- Ultra-Low Saturation Voltage V_{CE(sat)} < 45mV @ 1A
- High Current R_{CE(sat)} = 23mΩ Typical
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Rated to +175°C Ideal for High-Temperature Environments
- Complementary PNP Type: <u>DXTP80100CFGQ</u>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DXTN80100CFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

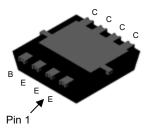
- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)

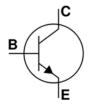
Applications

- MOSFET & IGBT gate drivers
- Load switches
- Low-voltage regulation
- DC to DC converters
- Motors, solenoids, relays and actuator drivers control

PowerDI3333-8/SWP (Type UX)







Top View Bottom View Device Symbol

Ordering Information (Note 4)

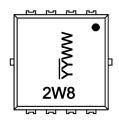
Orderable Part Number	Package	Marking	Bool Size (inches)	Toma Middle (mane)	Packing	
Orderable Part Number			Reel Size (inches)	rape width (mm)	Qty.	Carrier
DXTN80100CFGQ-7	PowerDI3333-8/SWP (Type UX)	2W8	7	12	2,000	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8/SWP (Type UX)



2W8 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 25 = 2025)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated in the United States and other countries.



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	150	V
Collector-Emitter Voltage	VCEO	100	V
Emitter-Base Voltage	VEBO	8	V
Continuous Collector Current (Note 5)	lc	3.5	Α
Continuous Collector Current (Note 7)	lc	5.5	Α
Peak Pulse Current	Ісм	10	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	(Note 5)		900	mW
Power Dissipation	(Note 6)	PD	1.6	W
	(Note 7)		2.4	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	92	°C/W
	(Note 7)		62.5	°C/W
Thermal Resistance, Junction to Case (Note 7)	·	Rejc	6.5	°C/W
Thermal Resistance, Junction to Lead (Note 8)		Rejl	4.2	°C/W
Operating and Storage Temperature Range		TJ, Tstg	-55 to +175	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С
Electrostatic Discharge - Charged Device Model	ESD CDM	1,000	V	IV

Notes:

- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady state.
- 6. Same as Note 5, except the device is mounted on 15mm x 15mm 2oz copper. 7. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

- 8. Thermal resistance from junction to solder-point (at the collector tab).
 9. Refer to JEDEC specifications JESD22-A114, JESD22-A115 and JESD22-C101.



Thermal Characteristics and Derating Information

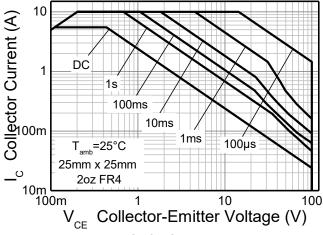


Fig 1. Safe Operating Area

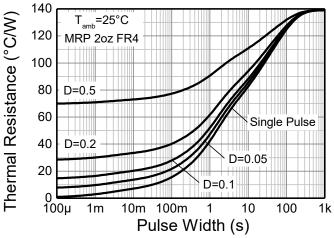


Fig 2. Transient Thermal Impedance

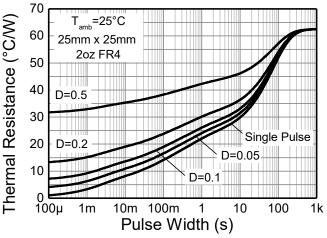


Fig 3. Transient Thermal Impedance

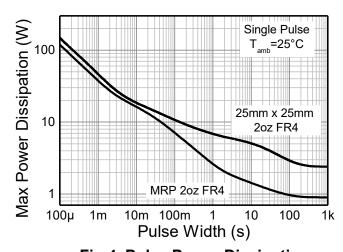


Fig 4. Pulse Power Dissipation

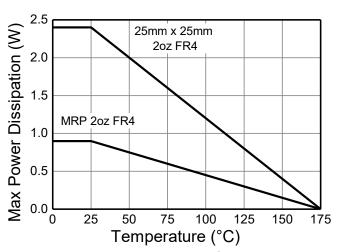


Fig 5. Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	ВУсво	150	_	_	V	I _C = 100μA	
Collector-Emitter Breakdown Voltage (Note 10)	BVceo	100	_	_	V	Ic = 10mA	
Emitter-Collector Breakdown Voltage	BVECO	5	_	_	V	I _E = 100μA	
Emitter-Base Breakdown Voltage	ВУЕВО	8	_	_	V	I _E = 100μA	
Collector Cutoff Current	Ісво	_	_	100	nA	V _{CB} = 150V	
Collector Cutoff Current		_	_	10	μΑ	V _{CB} = 150V, T _A = +125°C	
Collector Cutoff Current	Ices	_	_	300	nA	V _{CE} = 80V	
Emitter Cutoff Current	I _{EBO}	_	_	50	nA	V _{EB} = 7V	
	VCE(sat)	_	70	_	mV	I _C = 100mA, I _B = 1mA	
		_	80	140	mV	Ic = 1A, I _B = 20mA	
Collector Emitter Seturation Voltage (Note 10)		_	33	45	mV	I _C = 1A, I _B = 100mA	
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	_	110	160	mV	I _C = 3.5A, I _B = 175mA	
		_	130	180	mV	I _C = 5.5A, I _B = 550mA	
December 20 storestion Valle as (Nets 40)	V _{BE} (sat)	_	870	950	mV	I _C = 3.5A, I _B = 175mA	
Base-Emitter Saturation Voltage (Note 10)		_	970	1,050	mV	I _C = 5.5A, I _B = 550mA	
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	790	850	mV	Ic = 3.5A, VcE = 2V	
		_	850	950	mV	Ic = 5.5A, VcE = 2V	
	hFE	200	320	_	_	Ic = 10mA, VcE = 2V	
		250	310	420	_	I _C = 100mA, V _{CE} = 2V	
DC Current Cain (Note 10)		235	300	_	_	Ic = 1A, VcE = 2V	
DC Current Gain (Note 10)		110	190	_	_	Ic = 2A, VcE = 2V	
		40	80	_	_	I _C = 3.5A, V _{CE} = 2V	
		20	35	_		I _C = 5.5A, V _{CE} = 2V	
Input Capacitance	Cibo	_	640	_	pF	V _{EB} = 0.5V, f = 1MHz	
Output Capacitance	Cobo	_	24	_	pF	V _{CB} = 10V, f = 1MHz	
Current Gain-Bandwidth Product	f _T	100	125	_	MHz	V _{CE} = 10V, I _C = 100mA f = 50MHz	
Turn On Time	td	_	14	_	ns		
Turn-On Time	tr		210		ns	Vcc = 10V, Ic = 3.5A	
Turn Off Time	ts	_	440	_	ns	$I_{B1} = -I_{B2} = 350 \text{mA}$	
Turn-Off Time	t _f	_	110	_	ns		

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

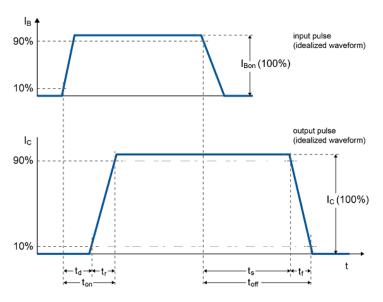
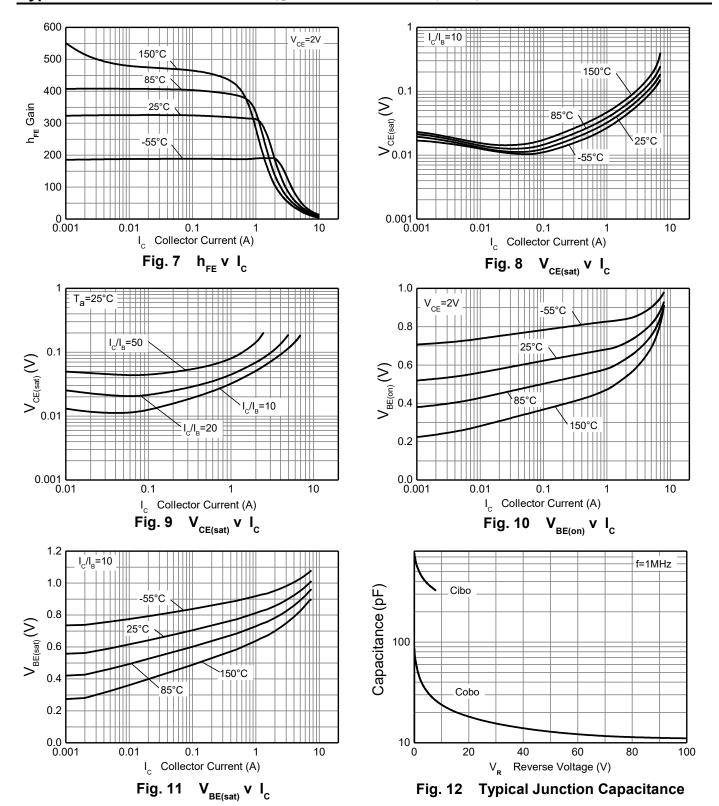


Fig 6. Timing Waveform



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





Typical Electrical Characteristics (continued) (@TA = +25°C, unless otherwise specified.)

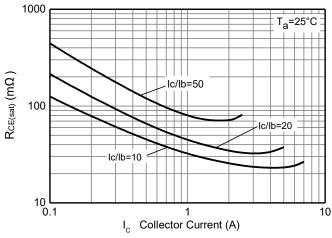


Fig. 13 $R_{CE(sat)} v I_{C}$

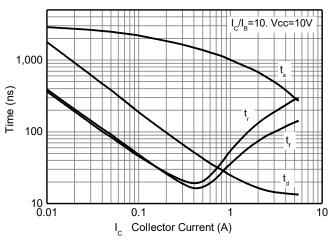


Fig. 15 Switching Performance

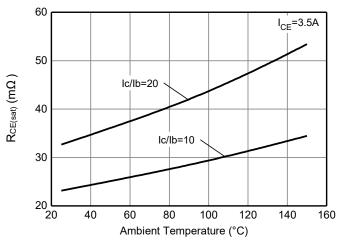


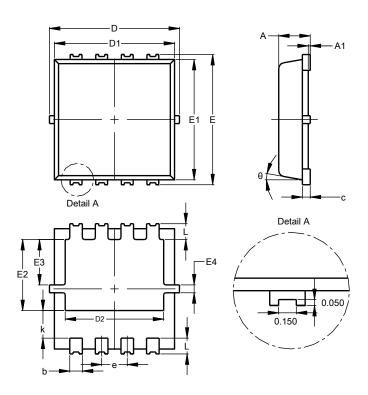
Fig. 14 R_{CE(sat)} v T_{amb}



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)

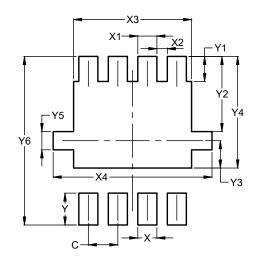


PowerDI3333-8/SWP							
(Type UX)							
Dim	Min	Max	Тур				
Α	0.75	0.85	0.80				
A1	0.00	0.05	-				
b	0.25	0.40	0.32				
С	0.10	0.25	0.15				
D	3.20	3.40	3.30				
D1	2.95	3.15	3.05				
D2	2.30	2.70	2.50				
E	3.20	3.40	3.30				
E1	2.95	3.15	3.05				
E2	1.60	2.00	1.80				
E3	0.95	1.35	1.15				
E4	0.10	0.30	0.20				
е	_	_	0.65				
k	0.50	0.90	0.70				
L	0.30	0.50	0.40				
θ	0°	12°	10°				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)



C 0.650	
X 0.420	
X1 0.420	
X2 0.230	
X3 2.600	
X4 3.500	
Y 0.700	
Y1 0.550	
Y2 1.650	
Y3 0.600	
Y4 2.450	
Y5 0.400	
Y6 3.700	

Notes:

- 11. For high-voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.
- 12. Side wall tin plated package for wettable flanks in AOI.



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